

## N - CHANNEL ENHANCEMENT MODE POWER MOS TRANSISTOR

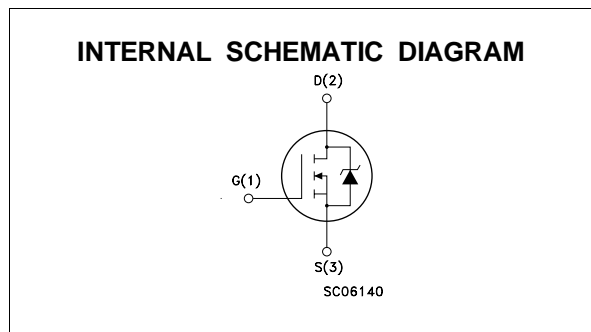
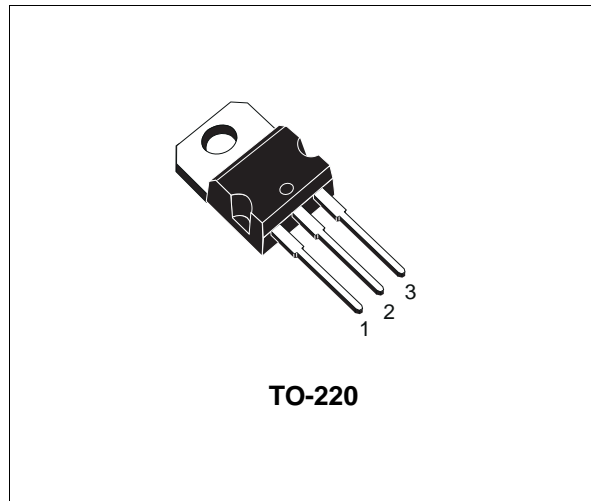
PRELIMINARY DATA

| TYPE        | V <sub>DSS</sub> | R <sub>DS(on)</sub> | I <sub>D</sub> |
|-------------|------------------|---------------------|----------------|
| STP60N05-14 | 50 V             | < 0.014 Ω           | 60 A           |
| STP60N06-14 | 60 V             | < 0.014 Ω           | 60 A           |

- TYPICAL R<sub>DS(on)</sub> = 0.012 Ω
- AVALANCHE RUGGED TECHNOLOGY
- 100% AVALANCHE TESTED
- REPETITIVE AVALANCHE DATA AT 100°C
- LOW GATE CHARGE
- HIGH CURRENT CAPABILITY
- 175 °C OPERATING TEMPERATURE
- VERY LOW R<sub>DS(on)</sub>
- APPLICATION ORIENTED CHARACTERIZATION

### APPLICATIONS

- HIGH CURRENT, HIGH SPEED SWITCHING
- SOLENOID AND RELAY DRIVERS
- REGULATORS
- DC-DC & DC-AC CONVERTERS
- MOTOR CONTROL, AUDIO AMPLIFIERS
- AUTOMOTIVE ENVIRONMENT (INJECTION, ABS, AIR-BAG, LAMPDRIVERS, Etc.)



### ABSOLUTE MAXIMUM RATINGS

| Symbol              | Parameter  | Value       |             | Unit |
|---------------------|--|-------------|-------------|------|
|                     |  | STP60N05-14 | STP60N06-14 |      |
| V <sub>DS</sub>     | Drain-Source Voltage (V <sub>GS</sub> = 0)           | 50          | 60          | V    |
| V <sub>DGR</sub>    | Drain-Gate Voltage (R <sub>GS</sub> = 20 KΩ)         | 50          | 60          | V    |
| V <sub>GS</sub>     | Gate-Source Voltage                                  | ± 20        |             | V    |
| I <sub>D</sub>      | Drain-Current (continuous) at T <sub>c</sub> = 25°C  | 60          |             | A    |
| I <sub>D</sub>      | Drain-Current (continuous) at T <sub>c</sub> = 100°C | 50          |             | A    |
| I <sub>DM</sub> (•) | Drain-Current (Pulsed)                               | 240         |             | A    |
| P <sub>tot</sub>    | Total Dissipation at T <sub>c</sub> = 25°C           | 150         |             | W/°C |
|                     | Derating Factor                                      | 1           |             | °C   |
| V <sub>ISO</sub>    | Insulation Withstand Voltage (DC)                    | -           |             | V    |
| T <sub>stg</sub>    | Storage Temperature                                  | -65 to 175  |             | °C   |
| T <sub>j</sub>      | Max Operating Junction Temperature                   | 175         |             | °C   |

(•)Pulse width limited by safe operating area

## STP60N05-14/STP60N06-14

### THERMAL DATA

|                       |  |     |      |      |
|-----------------------|--|-----|------|------|
| R <sub>thj-case</sub> | Thermal Resistance Junction-case               | Max | 1    | °C/W |
| R <sub>thj-amb</sub>  | Thermal Resistance Junction-ambient            | Max | 62.5 | °C/W |
| R <sub>thj-amb</sub>  | Thermal Resistance Case-sink                   | Typ | 0.5  | °C/W |
| T <sub>l</sub>        | Maximum Lead Temperature For Soldering Purpose |     | 300  | °C   |

### AVALANCHE CHARACTERISTICS

| Symbol          | Parameter  | Max Value | Unit |
|-----------------|--|-----------|------|
| I <sub>AR</sub> | Avalanche Current, Repetitive or Not-Repetitive (pulse width limited by T <sub>j</sub> max, δ < 1%)                          | 60        | A    |
| E <sub>AS</sub> | Single Pulse Avalanche Energy (starting T <sub>j</sub> = 25 °C, I <sub>D</sub> = I <sub>AR</sub> , V <sub>DD</sub> = 25 V)   | 600       | mJ   |
| E <sub>AR</sub> | Repetitive Avalanche Energy (pulse width limited by T <sub>j</sub> max, δ < 1%)  | 150       | mJ   |
| I <sub>AR</sub> | Avalanche Current, Repetitive or Not-Repetitive (T <sub>c</sub> = 100 °C, pulse width limited by T <sub>j</sub> max, δ < 1%) | 50        | A    |

### ELECTRICAL CHARACTERISTICS (T<sub>case</sub> = 25 °C unless otherwise specified)

OFF

| Symbol               | Parameter   | Test Conditions  | Min. | Typ. | Max.        | Unit     |
|----------------------|---|--|------|------|-------------|----------|
| V <sub>(BR)DSS</sub> | Drain-source Breakdown Voltage                        | I <sub>D</sub> = 250 μA V <sub>GS</sub> = 0  | 60   |      |             | V        |
| I <sub>DSS</sub>     | Zero Gate Voltage Drain Current (V <sub>GS</sub> = 0) | V <sub>DS</sub> = Max Rating<br>V <sub>DS</sub> = Max Rating x 0.8 T <sub>c</sub> = 125 °C |      |      | 250<br>1000 | μA<br>μA |
| I <sub>GSS</sub>     | Gate-body Leakage Current (V <sub>DS</sub> = 0)       | V <sub>GS</sub> = ± 20 V   |      |      | 100         | nA       |

ON (\*)

| Symbol              | Parameter                         | Test Conditions  | Min. | Typ.  | Max.           | Unit   |
|---------------------|-----------------------------------|--|------|-------|----------------|--------|
| V <sub>GS(th)</sub> | Gate Threshold Voltage            | V <sub>DS</sub> = V <sub>GS</sub> I <sub>D</sub> = 250 μA  | 2    | 3     | 4              | V      |
| R <sub>DS(on)</sub> | Static Drain-source On Resistance | V <sub>GS</sub> = 10 V I <sub>D</sub> = 30 A<br>V <sub>GS</sub> = 10 V I <sub>D</sub> = 30 A T <sub>c</sub> = 100 °C |      | 0.012 | 0.014<br>0.028 | Ω<br>Ω |
| I <sub>D(on)</sub>  | On State Drain Current            | V <sub>DS</sub> > I <sub>D(on)</sub> x R <sub>DS(on)max</sub><br>V <sub>GS</sub> = 10 V                              | 60   |       |                | A      |

### DYNAMIC

| Symbol              | Parameter                    | Test Conditions   | Min. | Typ. | Max. | Unit |
|---------------------|------------------------------|---|------|------|------|------|
| g <sub>fs</sub> (*) | Forward Transconductance     | V <sub>DS</sub> > I <sub>D(on)</sub> x R <sub>DS(on)max</sub> I <sub>D</sub> = 30 A | 20   | 30   |      | S    |
| C <sub>iss</sub>    | Input Capacitance            | V <sub>DS</sub> = 25 V f = 1 MHz V <sub>GS</sub> = 0                                |      | 3900 | 4800 | pF   |
| C <sub>oss</sub>    | Output Capacitance           |   |      | 950  | 1200 | pF   |
| C <sub>rss</sub>    | Reverse Transfer Capacitance |   |      | 250  | 320  | pF   |

**ELECTRICAL CHARACTERISTICS** (continued)**SWITCHING ON**

| Symbol                        | Parameter  | Test Conditions   | Min. | Typ.            | Max.      | Unit             |
|-------------------------------|--|---|------|-----------------|-----------|------------------|
| $t_{d(on)}$<br>$t_r$          | Turn-on Time<br>Rise Time                                    | $V_{DD} = 25\text{ V}$<br>$R_G = 4.7\ \Omega$                     |      | 30<br>180       | 50<br>250 | ns<br>ns         |
| $(di/dt)_{on}$                | Turn-on Current Slope  | $V_{DD} = 40\text{ V}$<br>$R_G = 47\ \Omega$                      |      | 210             |           | A/ $\mu\text{s}$ |
| $Q_g$<br>$Q_{gs}$<br>$Q_{gd}$ | Total Gate Charge<br>Gate-Source Charge<br>Gate-Drain Charge | $V_{DD} = 40\text{ V}$ $I_D = 60\text{ A}$ $V_{GS} = 10\text{ V}$ |      | 130<br>26<br>55 | 170       | nC<br>nC<br>nC   |

**SWITCHING OFF**

| Symbol                          | Parameter   | Test Conditions                               | Min. | Typ.             | Max.             | Unit           |
|---------------------------------|---|---|------|------------------|------------------|----------------|
| $t_{r(Voff)}$<br>$t_f$<br>$t_c$ | Off-voltage Rise Time<br>Fall Time<br>Cross-over Time | $V_{DD} = 40\text{ V}$<br>$R_G = 4.7\ \Omega$ |      | 35<br>135<br>180 | 50<br>190<br>250 | ns<br>ns<br>ns |

**SOURCE DRAIN DIODE**

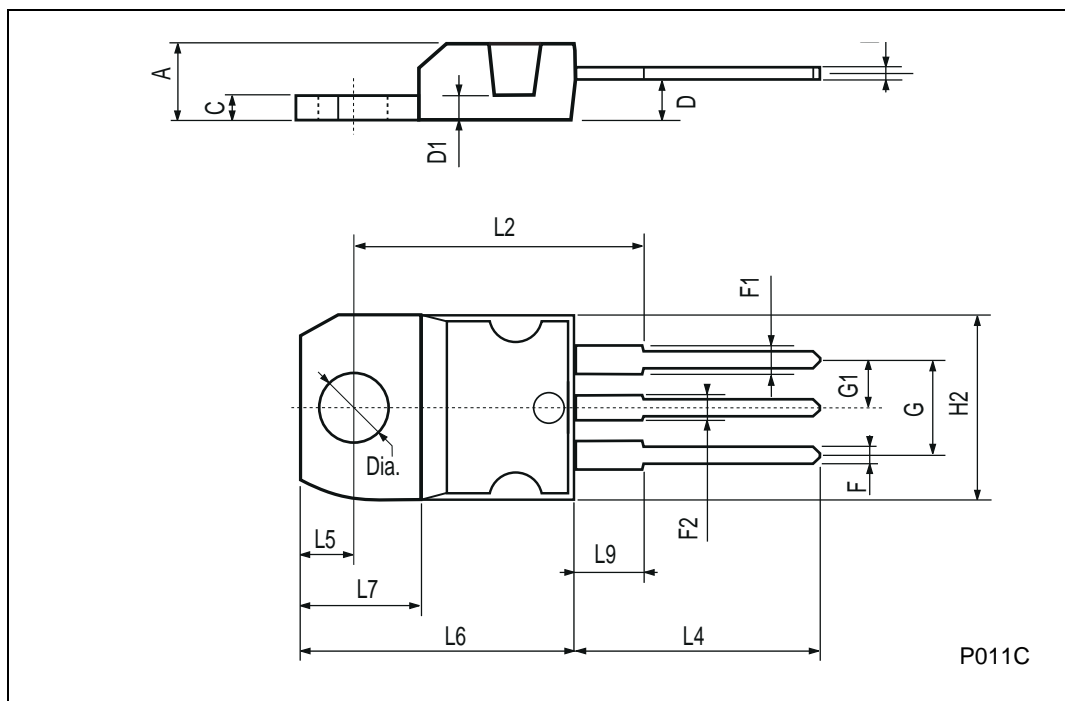
| Symbol                            | Parameter  | Test Conditions  | Min. | Typ.             | Max.      | Unit                     |
|-----------------------------------|--|--|------|------------------|-----------|--------------------------|
| $I_{SD}$<br>$I_{SDM}(\bullet)$    | Source-drain Current<br>Source-drain Current (pulsed)                        |  |      |                  | 60<br>240 | A<br>A                   |
| $V_{SD} (*)$                      | Forward On Voltage   | $I_{SD} = 60\text{ A}$ $V_{GS} = 0$  |      |                  | 1.6       | V                        |
| $t_{rr}$<br>$Q_{rr}$<br>$I_{RRM}$ | Reverse Recovery Time<br>Reverse Recovery Charge<br>Reverse Recovery Current | $I_{SD} = 60\text{ A}$ $V_{DD} = 30\text{ V}$<br>$di/dt = 100\text{ A}/\mu\text{s}$<br>$T_j = 150\text{ }^\circ\text{C}$ |      | 150<br>0.56<br>9 |           | ns<br>$\mu\text{C}$<br>A |

(\*) Pulsed: Pulse duration = 300  $\mu\text{s}$ , duty cycle 1.5 %

(\bullet) Pulse width limited by safe operating area

**TO-220 MECHANICAL DATA**

| DIM. | mm    |      |       | inch  |       |       |
|------|-------|------|-------|-------|-------|-------|
|      | MIN.  | TYP. | MAX.  | MIN.  | TYP.  | MAX.  |
| A    | 4.40  |      | 4.60  | 0.173 |       | 0.181 |
| C    | 1.23  |      | 1.32  | 0.048 |       | 0.051 |
| D    | 2.40  |      | 2.72  | 0.094 |       | 0.107 |
| D1   |       | 1.27 |       |       | 0.050 |       |
| E    | 0.49  |      | 0.70  | 0.019 |       | 0.027 |
| F    | 0.61  |      | 0.88  | 0.024 |       | 0.034 |
| F1   | 1.14  |      | 1.70  | 0.044 |       | 0.067 |
| F2   | 1.14  |      | 1.70  | 0.044 |       | 0.067 |
| G    | 4.95  |      | 5.15  | 0.194 |       | 0.203 |
| G1   | 2.4   |      | 2.7   | 0.094 |       | 0.106 |
| H2   | 10.0  |      | 10.40 | 0.393 |       | 0.409 |
| L2   |       | 16.4 |       |       | 0.645 |       |
| L4   | 13.0  |      | 14.0  | 0.511 |       | 0.551 |
| L5   | 2.65  |      | 2.95  | 0.104 |       | 0.116 |
| L6   | 15.25 |      | 15.75 | 0.600 |       | 0.620 |
| L7   | 6.2   |      | 6.6   | 0.244 |       | 0.260 |
| L9   | 3.5   |      | 3.93  | 0.137 |       | 0.154 |
| DIA. | 3.75  |      | 3.85  | 0.147 |       | 0.151 |



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